MJD2955 (PNP)
MJD3055 (NPN)

Complementary Power Transistors

DPAK For Surface Mount Applications

Designed for general purpose amplifier and low speed switching applications.

Features

- Lead Formed for Surface Mount Applications in Plastic Sleeves (No Suffix)
- Straight Lead Version in Plastic Sleeves ("−1" Suffix)
- Electrically Similar to MJE2955 and MJE3055
- DC Current Gain Specified to 10 Amperes
- High Current Gain−Bandwidth Product − f_T = 2.0 MHz (Min) @ I_C = 500 mAdc
- Epoxy Meets UL 94 V−0 @ 0.125 in
- ESD Ratings: Human Body Model, 3B > 8000 V
  Machine Model, C > 400 V
- These are Pb−Free Packages

MAXIMUM RATINGS

Rating	Symbol	Max	Unit
Collector−Emitter Voltage	V_{CEO}	60	Vdc
Collector−Base Voltage	V_{CB}	70	Vdc
Emitter−Base Voltage	V_{EB}	5	Vdc
Collector Current	I_C	10	Adc
Base Current	I_B	6	Adc
Total Power Dissipation @ T_C = 25°C Derate above 25°C	P_D†	20 0.16	W W/°C
Total Power Dissipation (Note1) @ T_A = 25°C Derate above 25°C	P_D	 1.75 0.014	W W/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction−to−Case	$R_{\theta JC}$	6.25	°C/W
Thermal Resistance, Junction−to−Ambient (Note1)	$R_{\theta JA}$	71.4	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

†Safe Area Curves are indicated by Figure 1. Both limits are applicable and must be observed.

1. These ratings are applicable when surface mounted on the minimum pad sizes recommended.

ON Semiconductor®

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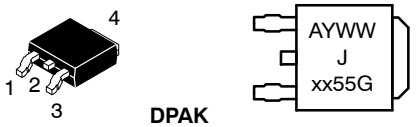
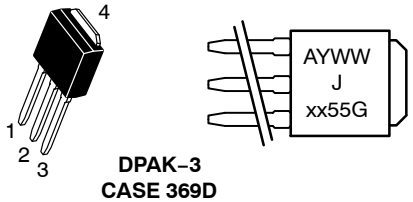
SILICON
POWER TRANSISTORS
10 AMPERES
60 VOLTS, 20 WATTS

MARKING DIAGRAMS



DPAK
CASE 369C
STYLE 1



DPAK−3
CASE 369D
STYLE 1

A = Assembly Location
Y = Year
WW = Work Week
Jxx55 = Device Code
x = 29 or 30
G = Pb−Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Sustaining Voltage (Note 2) (I_C = 30 mAdc, I_B = 0)	$V_{CEO(sus)}$	60	–	Vdc
Collector Cutoff Current (V_{CE} = 30 Vdc, I_B = 0)	I_{CEO}	–	50	μAdc
Collector Cutoff Current (V_{CE} = 70 Vdc, $V_{EB(off)}$ = 1.5 Vdc) (V_{CE} = 70 Vdc, $V_{EB(off)}$ = 1.5 Vdc, T_C = 150°C)	I_{CEX}	 – –	 0.02 2	mAdc
Collector Cutoff Current (V_{CB} = 70 Vdc, I_E = 0) (V_{CB} = 70 Vdc, I_E = 0, T_C = 150°C)	I_{CBO}	 – –	 0.02 2	mAdc
Emitter Cutoff Current (V_{BE} = 5 Vdc, I_C = 0)	I_{EBO}	–	0.5	mAdc
ON CHARACTERISTICS				
DC Current Gain (Note 2) (I_C = 4 Adc, V_{CE} = 4 Vdc) (I_C = 10 Adc, V_{CE} = 4 Vdc)	h_{FE}	 20 5	 100 –	–
Collector–Emitter Saturation Voltage (Note 2) (I_C = 4 Adc, I_B = 0.4 Adc) (I_C = 10 Adc, I_B = 3.3 Adc)	$V_{CE(sat)}$	 – –	 1.1 8	Vdc
Base–Emitter On Voltage (Note 2) (I_C = 4 Adc, V_{CE} = 4 Vdc)	$V_{BE(on)}$	–	1.8	Vdc
DYNAMIC CHARACTERISTICS				
Current–Gain – Bandwidth Product (I_C = 500 mAdc, V_{CE} = 10 Vdc, f = 500 kHz)	f_T	2	–	MHz

2. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.

ORDERING INFORMATION

Device	Package Type	Package	Shipping†
MJD2955G	DPAK (Pb–Free)	369C	75 Units / Rail
MJD2955–1G	DPAK (Pb–Free)	369D	
MJD2955T4G	DPAK (Pb–Free)	369C	2500 Tape & Reel
MJD3055G	DPAK (Pb–Free)		75 Units / Rail
MJD3055T4G	DPAK (Pb–Free)		2500 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

TYPICAL CHARACTERISTICS

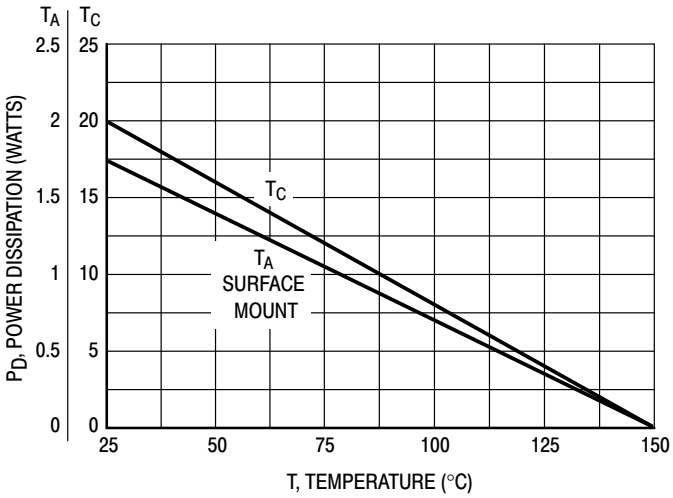


Figure 1. Power Derating

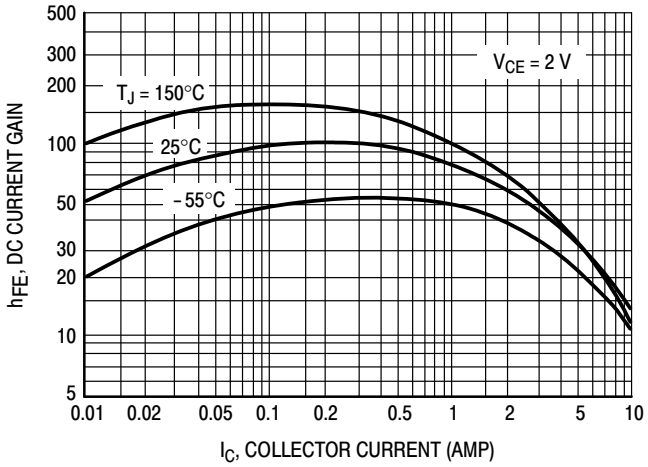


Figure 2. DC Current Gain

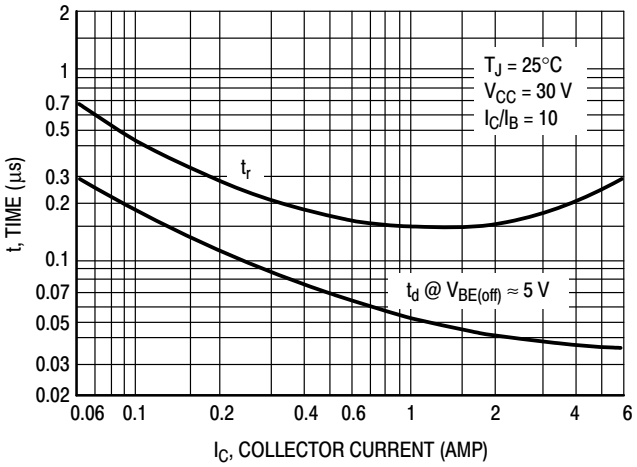


Figure 3. Turn−On Time

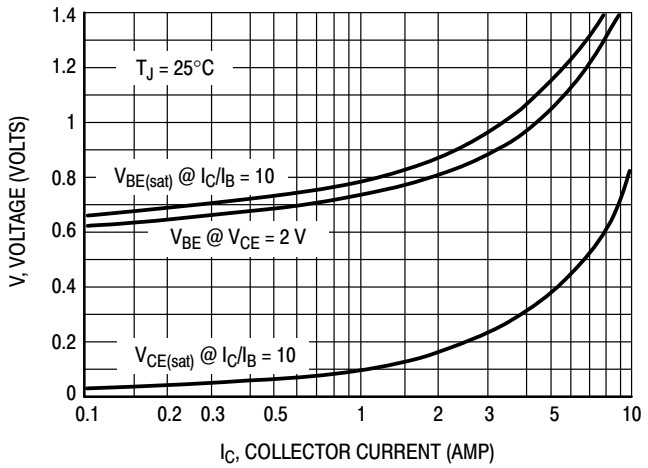


Figure 4. “On” Voltages, MJD3055

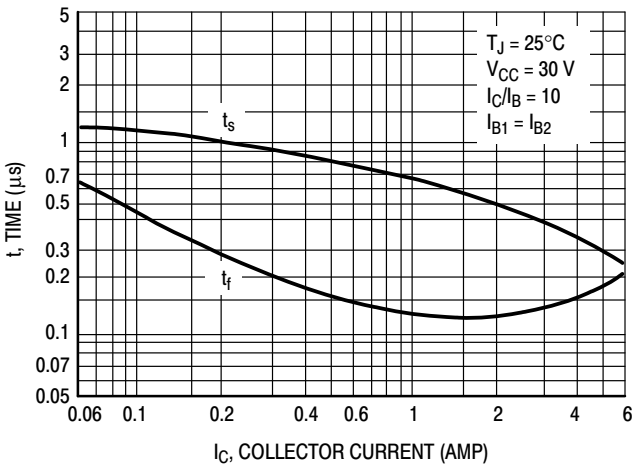


Figure 5. Turn−Off Time

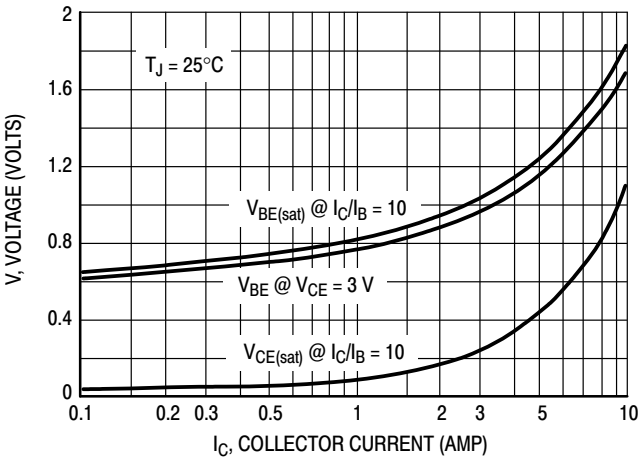


Figure 6. "On" Voltages, MJD2955

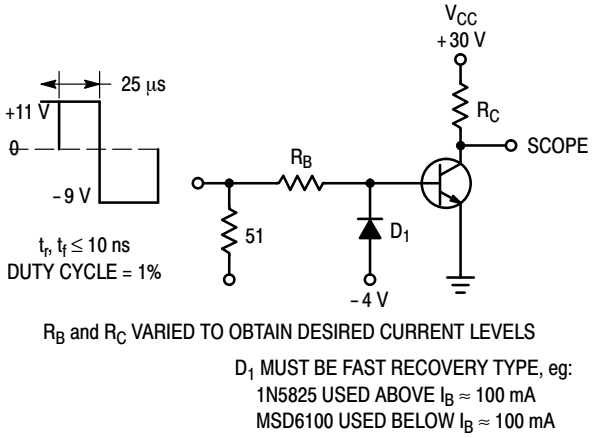


Figure 7. Switching Time Test Circuit

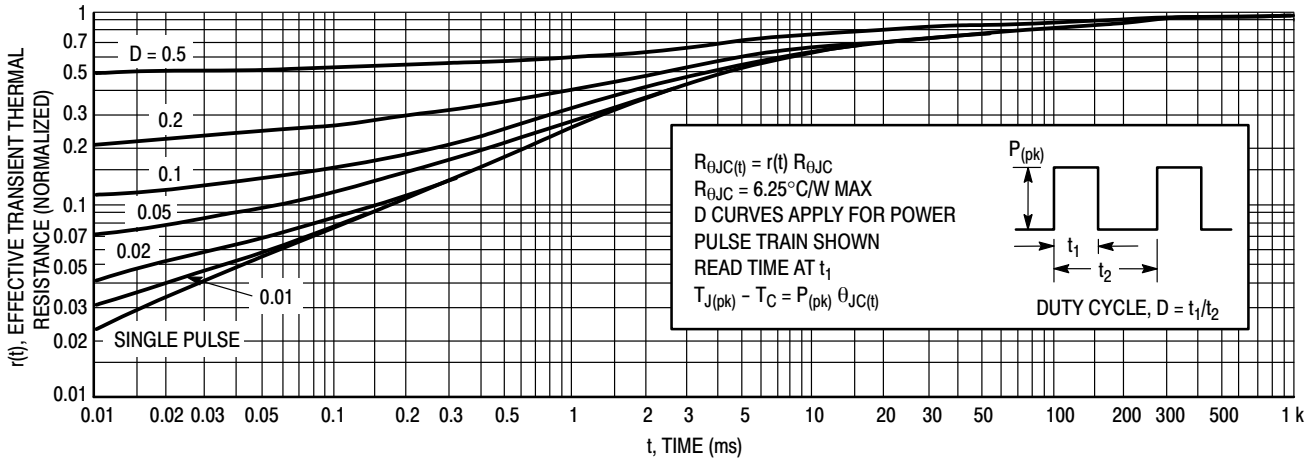


Figure 8. Thermal Response

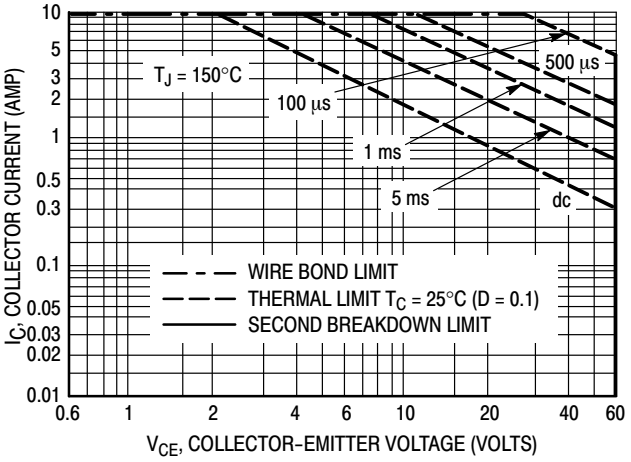


Figure 9. Maximum Forward Bias Safe Operating Area

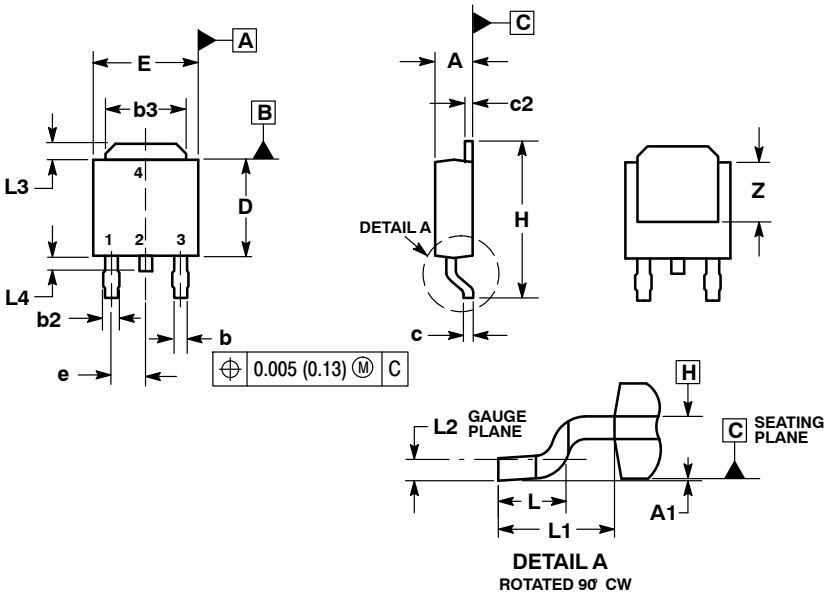
FORWARD BIAS SAFE OPERATING AREA INFORMATION

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 9 is based on $T_{J(pk)} = 150°C$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150°C$. $T_{J(pk)}$ may be calculated from the data in Figure 8. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

PACKAGE DIMENSIONS

DPAK
CASE 369C−01
ISSUE D

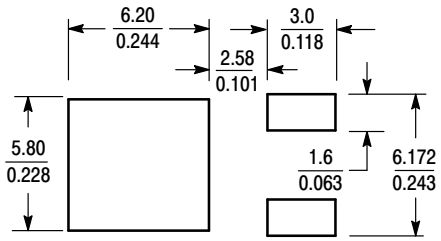


NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3 and Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.030	0.045	0.76	1.14
b3	0.180	0.215	4.57	5.46
c	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090 BSC		2.29 BSC	
H	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.108 REF		2.74 REF	
L2	0.020 BSC		0.51 BSC	
L3	0.035	0.050	0.89	1.27
L4	−−−	0.040	−−−	1.01
Z	0.155	−−−	3.93	−−−

STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

SOLDERING FOOTPRINT*



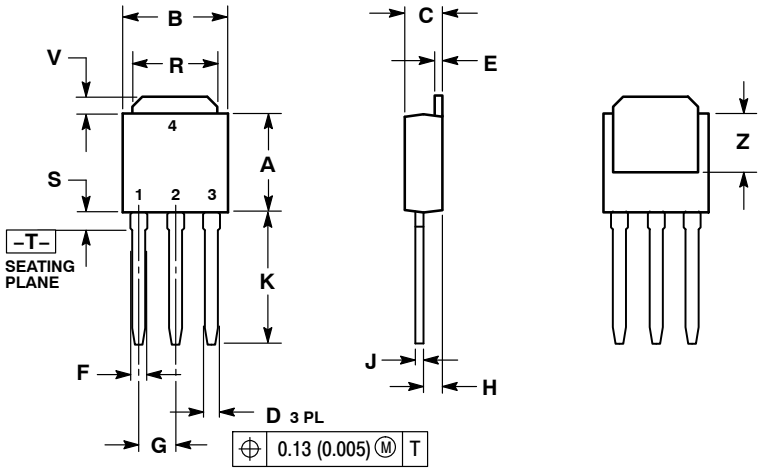
SCALE 3:1 (mm / inches)

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MJD2955 (PNP) MJD3055 (NPN)

PACKAGE DIMENSIONS

DPAK−3
CASE 369D−01
ISSUE B



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.235	0.245	5.97	6.35
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.090 BSC		2.29 BSC	
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.180	0.215	4.45	5.45
S	0.025	0.040	0.63	1.01
V	0.035	0.050	0.89	1.27
Z	0.155	−−−	3.93	−−−

STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
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